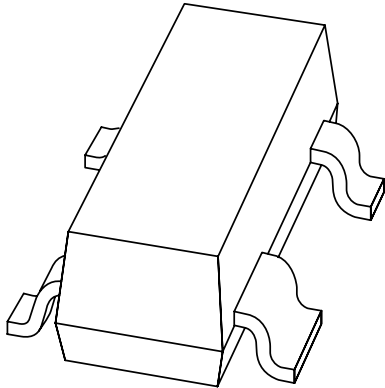


DATA SHEET



BAT74

Schottky barrier double diode

Product specification
Supersedes data of March 1991

1996 Mar 19

Schottky barrier double diode

BAT74

FEATURES

- Low forward voltage
- Guard ring protected
- Small SMD package.

APPLICATIONS

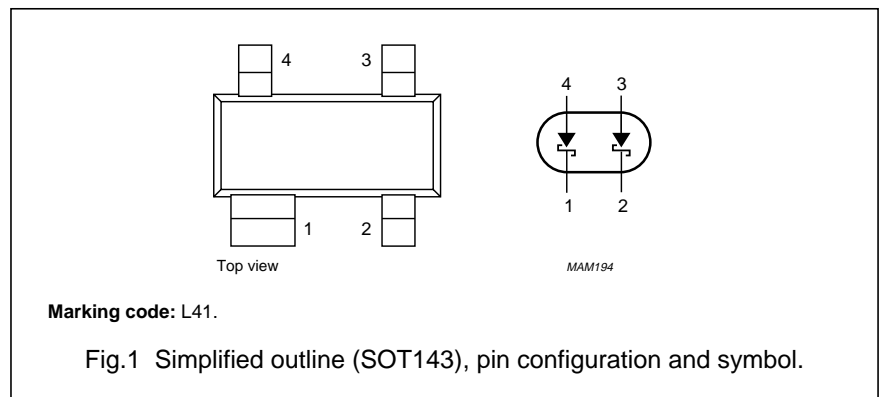
- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes.

DESCRIPTION

Planar Schottky barrier double diode. Two separate dies encapsulated in a SOT143 small plastic SMD package.

PINNING

PIN	DESCRIPTION
1	cathode (k ₁)
2	cathode (k ₂)
3	anode (a ₂)
4	anode (a ₁)



Schottky barrier double diode

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage		–	30	V
I_F	continuous forward current		–	200	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s}; \delta \leq 0.5$	–	300	mA
I_{FSM}	non-repetitive peak forward current	$t_p < 10 \text{ ms}$		600	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ °C}; \text{ see Fig.2}$	–	230	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	125	°C
T_{amb}	operating ambient temperature		–65	+125	°C
Double diode operation					
V_R	continuous reverse voltage		–	30	V
		series connection	–	60	V
I_F	continuous forward current		–	110 ⁽¹⁾	mA
I_{FRM}	repetitive peak forward current	$t_p \leq 1 \text{ s}; \delta \leq 0.5$	–	200	mA

Note

1. If both diodes are in forward operation at the same moment, total device current is max. 110 mA. If one diode is in reverse and the other in forward operation at the same moment, total device current is max. 200 mA.

Schottky barrier double diode

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ELECTRICAL CHARACTERISTICS $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
Per diode				
V_F	forward voltage	see Fig.3		
		$I_F = 0.1\text{ mA}$	240	mV
		$I_F = 1\text{ mA}$; note 1	320	mV
		$I_F = 10\text{ mA}$	400	mV
		$I_F = 30\text{ mA}$	500	mV
		$I_F = 100\text{ mA}$	800	mV
I_R	reverse current	$V_R = 25\text{ V}$; note 2; see Fig.4	2	μA
t_{rr}	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 10\text{ mA}$; $R_L = 100\ \Omega$; measured at $I_R = 1\text{ mA}$; see Fig.6	5	ns
C_d	diode capacitance	$f = 1\text{ MHz}$; $V_R = 1\text{ V}$; see Fig.5	10	pF

Notes

- Temperature coefficient of forward voltage $-0.6\%/K$.
- Pulsed test: $t_p = 300\ \mu\text{s}$; $\delta = 0.02$.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

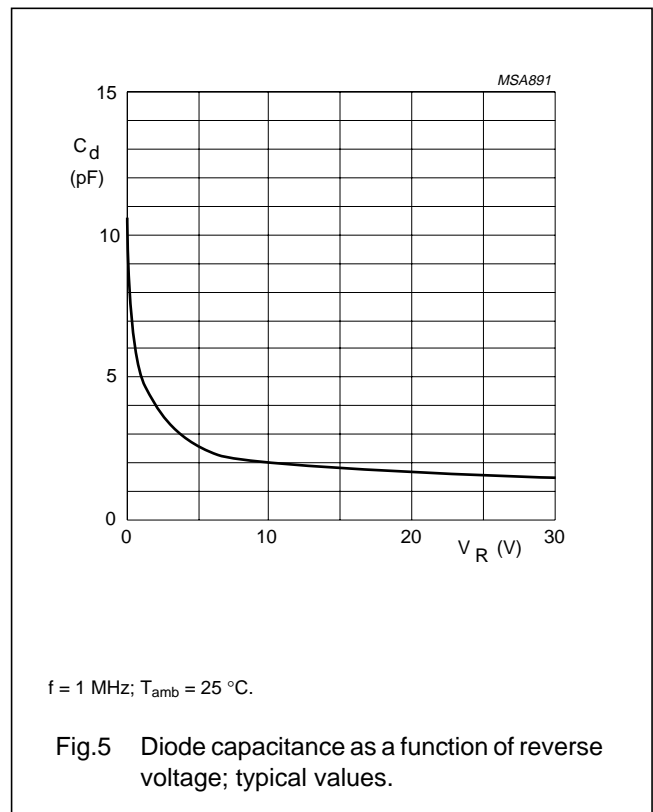
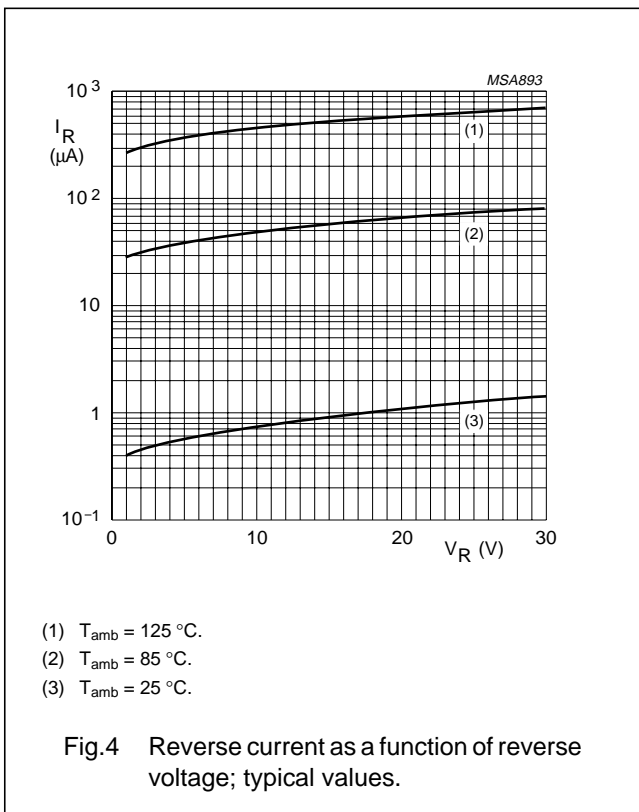
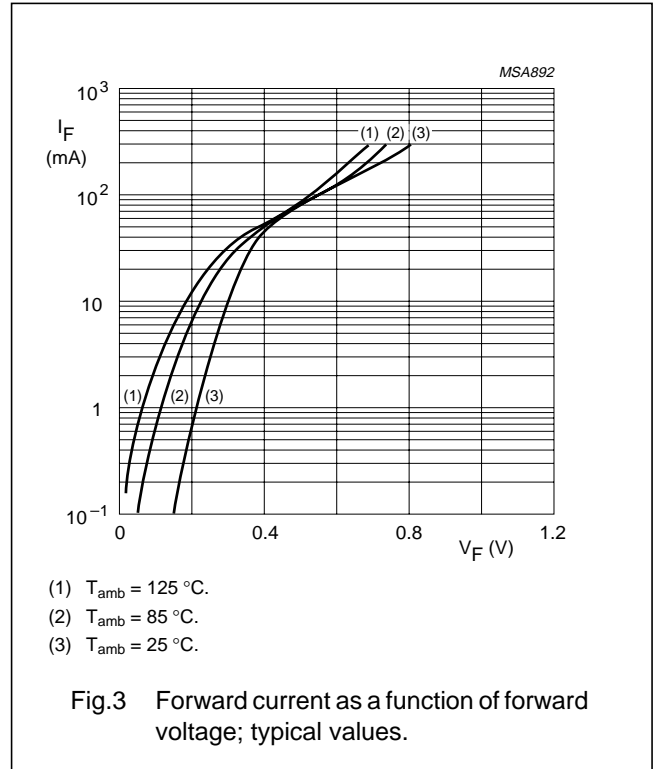
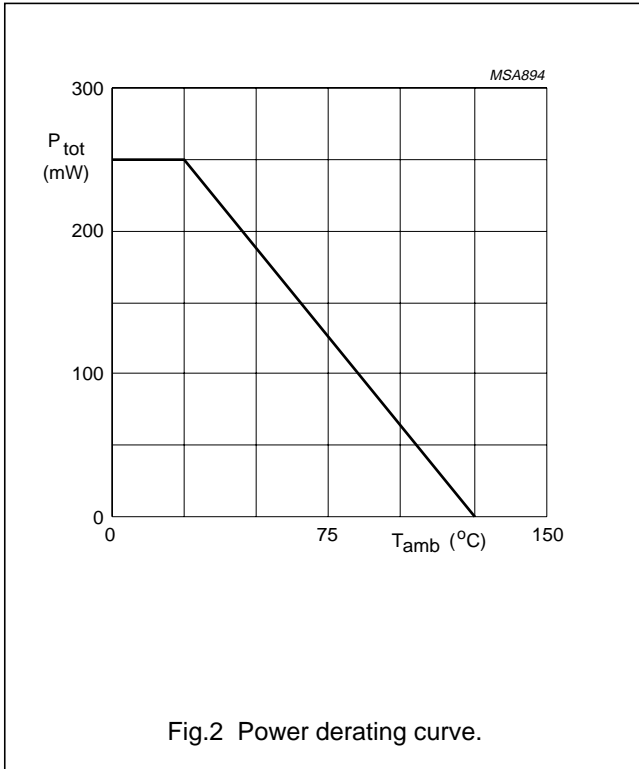
Note

- Refer to SOT143 standard mounting conditions .

Schottky barrier double diode

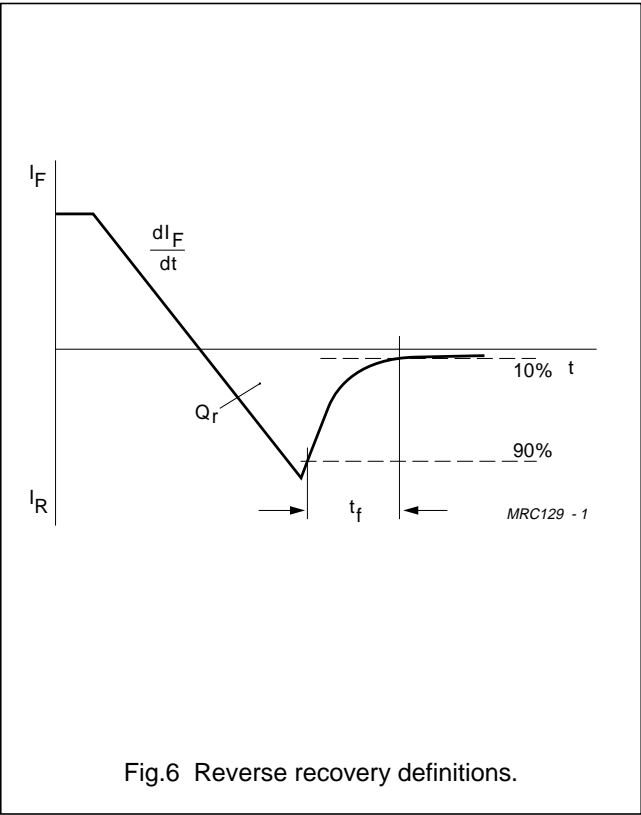
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GRAPHICAL DATA



Schottky barrier double diode

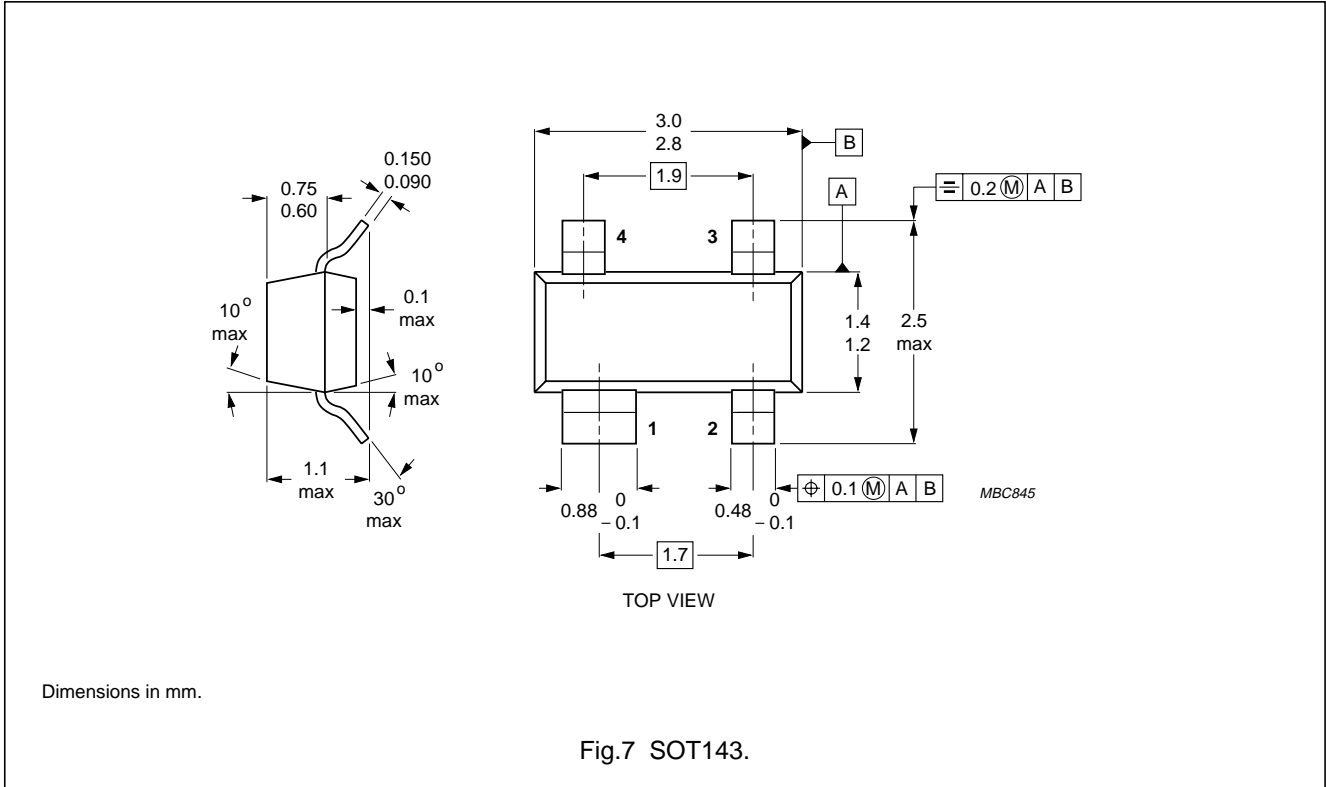
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Schottky barrier double diode

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PACKAGE OUTLINE



DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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